GLF1201Q



Product Specification

DESCRIPTION

POWER

The GLF1201Q is an advanced technology fully integrated I_QSmart^{TM} load switch device with True Reverse Current Blocking (TRCB) technology and the slew rate control of the output voltage. The best in class efficiency makes it an ideal choice for electronics requiring operation under the high temperature up to 125 °C.

The GLF1201Q offers an industry leading True Reverse Current Blocking (TRCB) performance, featuring an ultra-low threshold voltage. It minimizes reverse current flow in an event that the VOUT pin voltage exceeds the VIN voltage.

An integrated slew rate control can also enhance system reliability by mitigating bus voltage swings during switching events. Where uncontrolled switches can generate high inrush currents that result in voltage droop and/or bus reset events, the GLF slew rate control specifically limits inrush currents during turn-on to minimize voltage droop.

The GLF1201Q load switch device supports an industry leading wide input voltage range and helps to improve operating life and system robustness. Furthermore, one device can be used in multiple voltage rail applications which helps to simplify inventory management and reduces operating cost.

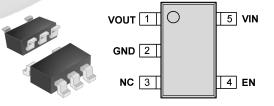
FEATURES

- AEC-Q100 Qualified
- Qualified for Automotive Applications: Temperature Grade 1: Ambient Operating Temperature Range: - 40 °C ~ +125 °C
- Wide Input Range: 1.5 V to 5.5 V 6 V abs max
- True Reverse Current Blocking
- R_{ON}: 60 mΩ Typ at 5.5 V_{IN}
- I_{OUT} Max: 2 A
- Ultra-Low I_Q : 0.48 μ A Typ at 5.5 V_{IN}
- Ultra-Low I_{SD}: 25 nA Typ at 5.5 V_{IN}
- Controlled Rise Time: 600 µs at 3.3VIN
- Internal EN Pull-Down Resistor on
- Integrated Output Discharge Switch
- ESD Performance Tested per AEC Q100 HBM: 4 kV, CDM: 2 kV
- Moisture Sensitivity Level: MSL-3 and 260 °C Peak Reflow Temp
- Lead-free, Halogen-free, and Adhere to RoHS
 Directive

APPLICATIONS

- Automotive Electronics
- Infotainment Systems
- Diagnosis System

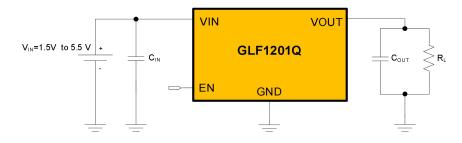




SOT23-5L

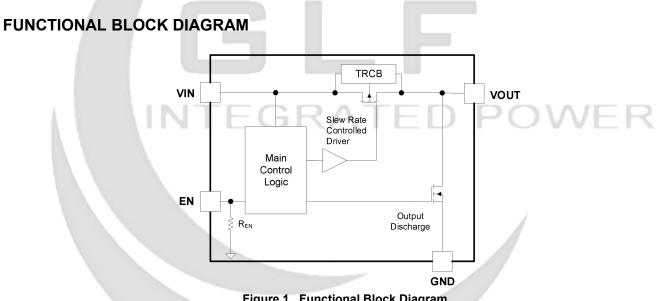


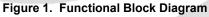
APPLICATION DIAGRAM



ALTERNATE DEVICE OPTIONS

Part Number	Top Mark	R _{oN} (Typ) at 5.5 V _{IN}	TRCB	Output Discharge	EN Activity
GLF1201Q-T1G7	DN	60 mΩ	Yes	85 Ω	High





PIN CONFIGURATION

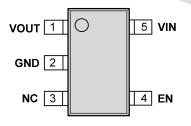


Figure 2. SOT23-5L

PIN DEFINITION

Pin #	Name	Description
1	VOUT	Switch Output
2	GND	Ground
3	NC	No connection
4	EN	Enable to control the switch
5	VIN	Switch Input. Supply Voltage for IC

GLF1201Q Nano Current Power I₀Smart[™] Switch with TRCB

ABSOLUTE MAXIMUM RATINGS

POWER

Stresses exceeding the absolute maximum ratings may damage the device. The device may not function or be operable above the recommended operating conditions; extended exposure to stresses above the recommended operating conditions may affect device reliability. The absolute maximum ratings are stress ratings only.

Symbol		Min.	Max.	Unit	
Vin	VIN, VOUT, VEN tO GND	VIN, VOUT, VEN tO GND			V
lout	Maximum Continuous Switch Curre	ent		2	А
T _{STG}	Storage Junction Temperature			150	°C
TJ	Operating Temperature Range			150	°C
θ _{JC}	Thermal Resistance, Junction to Case			90	°C/W
θյΑ	Thermal Resistance, Junction to Ambient			180	°C/W
	Electrostatia Discharge Canobility	Human Body Model, per AEC Q100-002	4		
ESD	Electrostatic Discharge Capability Charged Device Model, per AEC Q100-011				kV

Note. The θ_{JA} is measured at $T_A = 25^{\circ}$ C on a high effective thermal conductivity four-layer test board per JEDEC 51-7.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Min.	Max.	Unit
V _{IN}	Supply Voltage	1.5	5.5	V
TA	Ambient Operating Temperature	-40	+125	°C
1	INTEGRATED PO			2

ELECTRICAL CHARACTERISTICS

Values are at V_{IN} = 3.3V and T_A = 25°C unless otherwise noted.

Symbol	Parameter	Conditions			Тур.	Max.	Units	
Basic Ope	eration							
lo	Quiescent Current (1)	$V_{IN} = V_{EN} = 5.5 \text{ V}, I_{OUT} = 0 \text{ m}$	ıΑ		0.48	0.60		
IQ		$V_{IN}=V_{EN}=5.5 \text{ V}, I_{OUT}=0 \text{ mA}$	λ, Τ _Α = 125 °C		0.60		μA	
		V _{IN} =1.5 V, V _{EN} = 0 V, I _{OUT} =	=0 mA		2	20		
		V_{IN} =1.5 V, V_{EN} = 0 V, I_{OUT} =	=0 mA		3		nA	
Isd	Shut Down Current	V_{IN} =4.2 V, V_{EN} = 0 V, I_{OUT} =	=0 mA		10			
ISD	Shut Down Current	V _{IN} =5.5 V, V _{EN} = 0 V, I _{OUT} =0 mA			25	35		
		$V_{\text{IN}}{=}5.5$ V, V_{EN} = 0 V, $I_{\text{OUT}}{=}0$ mA, $T_{\text{A}}{=}85$ °C $^{(4)}$			0.30	0.45	μA	
		V _{IN} =5.5 V, V _{EN} = 0 V, I _{OUT} =0 mA, T _A =125 °C			2.30	3.00		
		V _{IN} =5.5 V, I _{OUT} = 500 mA	T _A =25 °C		60	68		
		VIN-5.5 V, IOUT- 500 IIIA	T _A = 125 °C		76			
		V -2 2 V I - 500 mA	T _A =25 °C		70	79		
		V _{IN} =3.3 V, I _{OUT} = 500 mA	T _A = 125 °C		90			
Ron	On-Resistance		1/-1.9/(1-200) mA	T _A =25 °C		110	124	mΩ
		V _{IN} =1.8 V, I _{OUT} = 300 mA	T _A = 125 °C		132			
		V _{IN} =1.5 V, I _{OUT} = 100 mA	T _A =25 °C		120	135		
		VIN-1.3 V, IOUT- 100 IIIA	T _A = 125 °C		155			



GLF1201Q

Nano Current Power I_QSmart[™] Switch with TRCB

Р	Output Discharge Desistance	V _{EN} =Low , I _{FORCE} = 10 mA		85		Ω
R _{DSC}	Output Discharge Resistance	V _{EN} =Low , I _{FORCE} = 10 mA, T _A = 125 °C		90		Ω
M		V _{IN} =1.5 V to 1.8 V, T _A = -40 °C to +125 °C	1.1			
VIH	EN Input Logic High Voltage	V _{IN} =1.8 V to 5.5 V, T _A = -40 °C to +125 °C	1.3			
		V _{IN} =1.5 V to 1.8 V, T _A = -40 °C to +125 °C			0.3	V
VIL	EN Input Logic Low Voltage	V _{IN} =1.8 V to 5.5 V, T _A = -40 °C to +125 °C			0.4	
Ren	EN Internal Resistance	Internal Pull-down Resistance		10		MΩ
I _{EN}	EN Current	V _{EN} =5.5 V		0.5		μA
	RCB Protection Threshold	Vout - Vin		42		
V _{RCB_TH}	Voltage	V _{OUT} - V _{IN,} T _A = 125 °C		50		
	RCB Protection Release	V _{IN} - V _{OUT}		22		mV
Vrcb_rl	Voltage	V _{IN} - V _{OUT} ,T _A = 125 °C		32		
Switching	Characteristics ^{(2), (3)}					
t _{dON}	Turn-On Delay			450		
t _R	Vout Rise Time	R _L =150 Ω, C _{OUT} =0.1 μF		600		1
t_{dOFF}	Turn-Off Delay ⁽⁴⁾			17		μs
t⊨	V _{OUT} Fall Time ^{(3), (4)}	Put Fall Time ^{(3), (4)} RL=150 Ω, C _{OUT} =0.1 μF		12		1
Notes:	1. Iq does not include the pull-dow	vn current of the enable pin through the R _{EN.}				1

2. $t_{ON} = t_{dON} + t_R$, $t_{OFF} = t_{dOFF} + t_F$ 3. Output discharge path is enabled when the device is enabled. Output discharge path is enabled when the set.
 By design; characterized, not production tested.

TIMING DIAGRAM

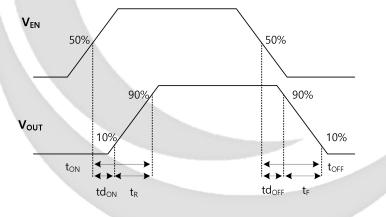


Figure 3. Timing Diagram

TYPICAL PERFORMANCE CHARACTERISTICS

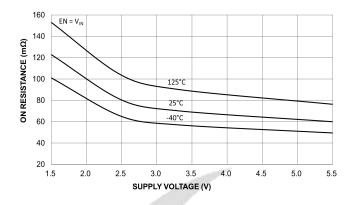


Figure 4. On-Resistance vs. Supply Voltage

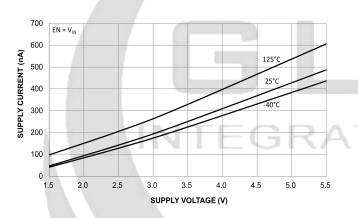


Figure 6. Quiescent Current vs. Supply Voltage

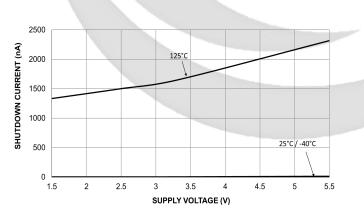
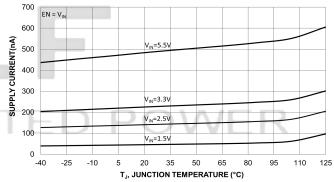
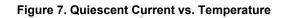


Figure 8. Shutdown Current vs. Supply Voltage

160 EN = V. 140 V_{IN}=1.5\ ON RESISTANCE (mΩ) 120 100 /_{IN}=2.5 80 V_{IN}=3.3\ V_{IN}=5.5 60 40 20 -40 -25 -10 5 20 35 50 80 95 110 125 65 T_J, JUNCTION TEMPERATURE (°C)

Figure 5. On-Resistance vs. Temperature





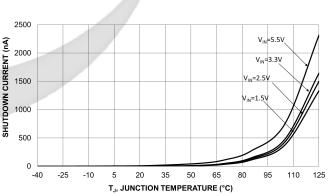
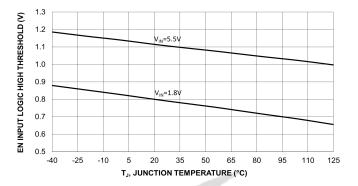


Figure 9. Shutdown Current vs. Temperature



INTEGRATED POWER

Figure 10. EN Input Logic High Threshold Vs. Temperature

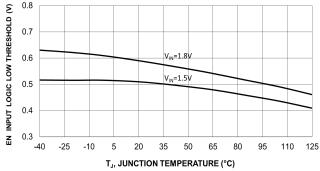


Figure 11. EN Input Logic Low Threshold Vs. Temperature

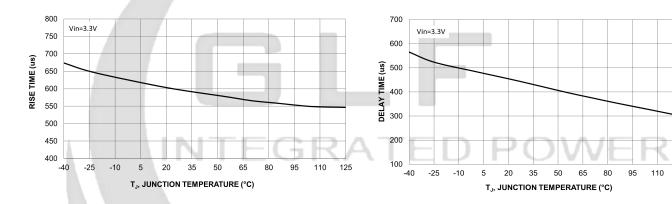


Figure 12. VOUT Rise Time vs. Temperature

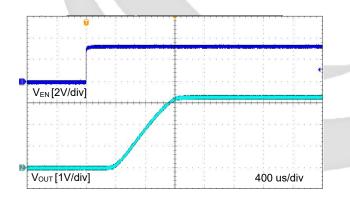
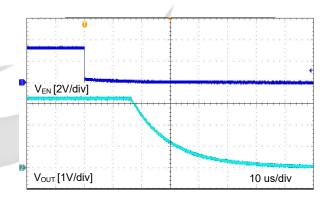
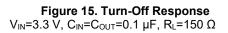


Figure 14. Turn-On Response $V_{\text{IN}}\text{=}3.3~\text{V},~C_{\text{IN}}\text{=}C_{\text{OUT}}\text{=}0.1~\mu\text{F},~\text{R}_{\text{L}}\text{=}150~\Omega$

Figure 13. Turn-On Delay Time vs. Temperature





125

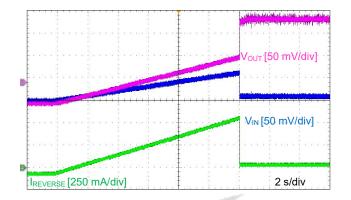


Figure 16. Reverse Current Blocking Threshold VIN=3.3 V, VOUT=Up to 3.4 V, CIN=COUT=0.1 μ F, RL=150 Ω

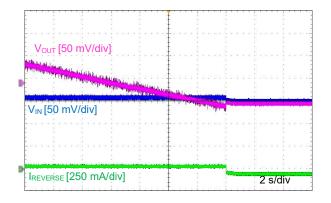


Figure 17. Reverse Current Blocking Release VIN=3.3 V, VOUT=Down to 3.2 V, CIN=COUT=0.1 μ F, RL=150 Ω

APPLICATION INFORMATION

The GLF1201Q integrated 2 A, ultra-efficient l_QSmart[™] load switch devices with a fixed slew rate control to limit the inrush current during turn on. It is capable of operating over a wide input range from 1.5 V to 5.5 V with low on-resistance to reduce conduction loss. In the off state, it consumes very low leakage current to lengthen the lifespan of a battery.

Input Capacitor

The GLF1201Q does not require an input capacitor. However, to reduce the voltage drop on the input power rail caused by transient inrush current at start-up, a 0.1 μ F capacitor is recommended to be placed close to the V_{IN} pin. A higher input capacitor value can be used to further attenuate the input voltage drop.

Output Capacitor

The GLF1201Q does not require an output capacitor. However, use of an output capacitor is recommended to mitigate voltage undershoot on the output pin when the switch is turning off. Undershoot can be caused by parasitic inductance from board traces or intentional load inductances. If load inductances do exist, use of an output capacitor can improve output voltage stability and system reliability. The C_{OUT} capacitor should be spaced close to the VOUT and GND pins.

EN pin

The GLF1201Q can be activated by forcing EN pin high level. Note that the EN pin has an internal pull-down resistor to help pull the main switch to a known "off state" when no EN signal is applied from an external controller.

True Reverse Current Blocking

The GLF1201Q has a built-in true reverse current blocking protection (TRCB) which always monitors the output voltage level regardless of the status of EN pin to check if it is greater than the input voltage. When the output voltage goes beyond the input voltage by 42 mV, the TRCB turns off the device immediately. Note that some reverse current can occur until the V_{RCB} is triggered. The main switch will resume normal operation when the output voltage drops below the input source by the TRCB protection release voltage.

Output Discharge Function

The GLF1201Q has an internal discharge NFET switch on the VOUT pin. When an EN signal turns off the main power switch, the NFET switch turns on to discharge an output capacitor quickly.

Thermal Consideration

The maximum power dissipation ($P_{D(MAX)}$) depends on specific temperature conditions such as ambient temperature, a silicon junction temperature, printed circuit board conditions, and a thermal resistance of an IC. It can be calculated by the following equation The maximum junction temperature of the GLF1201Q is not allowed to exceed the maximum rating, 150 °C to insure normal functionality.

The continuous output current given in Figure 18 shows current capability at the ambient temperature, T_A . It is limited by the maximum junction temperature, the thermal resistance, and the rise of the R_{ON} at the ambient temperature condition.

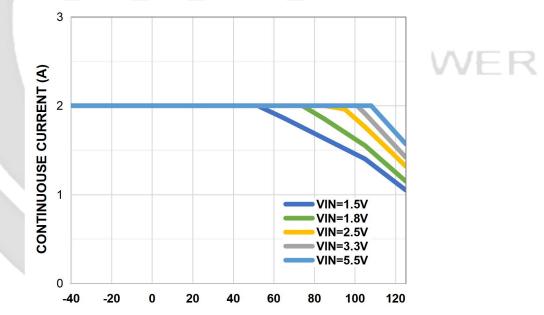
$$P_{D(max)} = \frac{T_{J(max)} - T_A}{\theta_{JA}}$$
$$I_{D(DC)} = \sqrt{\frac{T_{J(max)} - T_A}{R_{DS} \cdot \theta_{JA}}}$$

Where

T_{J(max)} : Maximum junction temperature

T_A : Ambient temperature

 θ_{JA} $\ \ :$ Thermal resistance between junction and ambient



Note. This graph is based on a high effective thermal conductivity four-layer test board per JEDEC 51-7.

Figure 18. Continuous Current vs. Ambient Temperature

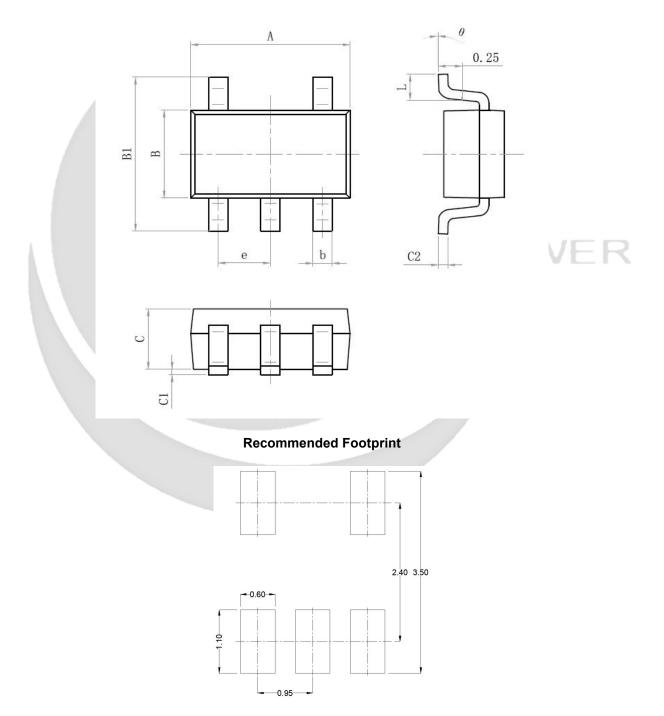
Board Layout

All traces should be as short as possible to minimize parasitic inductance effects. Wide traces for VIN, VOUT, and GND will help reduce signal degradation and parasitic effects during dynamic operation as well as improve the thermal performance at high load current.



PACKAGE OUTLINE

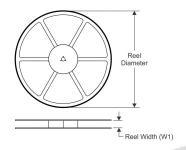
Size Mark	Min(mm)	Max(mm)	Size Mark	Min(mm)	Max(mm)
А	2.82	3.02	С	1.05	1.15
е	0.9	95 (BSC)	C1	0.03	0.15
b	0.28	0.45	C2	0.12	0.23
В	1.50	1.70	L	0.35	0.55
B1	2.60	3.00	θ	0°	8°

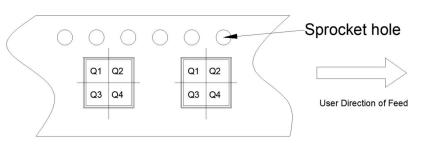


TAPE AND REEL INFORMATION

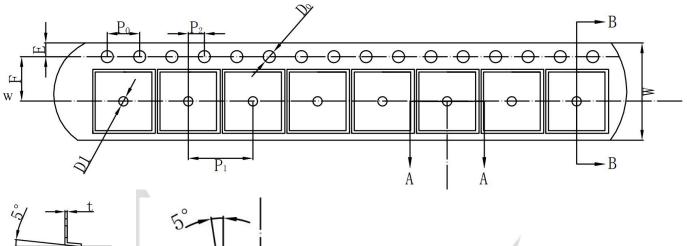
REEL DIMENSIONS

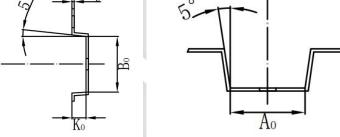
QUADRANT ASSIGNMENTS PIN 1 ORIENTATION TAPE





TAPE DIMENSIONS





Device	Package	Pins	SPQ	Reel Diameter (mm)	Reel Width W1	A0	В0	К0	P1	w	Pin1
GLF1201Q-T1G7	SOT23-5	5	3000	178	9	3.25	3.30	1.38	4	8	Q3

Remark:

- A0: Dimension designed to accommodate the component width
- B0: Dimension designed to accommodate the component length
- C0: Dimension designed to accommodate the component thickness
- W: Overall width of the carrier tape
- P1: Pitch between successive cavity centers



SPECIFICATION DEFINITIONS

Document Type	Meaning	Product Status
Target Specification	This is a target specification intended to support exploration and discussion of critical needs for a proposed or target device. Spec limits including typical, minimum, and maximum values are desired, or target, limits. GLF reserves the right to change limits at any time without warning or notification. A target specification in no way guarantees future production of the device in question.	Design / Development
Preliminary Specification	This is a draft version of a product specification. The specification is still under internal review and subject to change. GLF reserves the right to change the specification at any time without warning or notification. A preliminary specification in no way guarantees future production of the device in question.	Qualification
Product Specification	This document represents the anticipated production performance characteristics of the device.	Production

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